

## Silicon PNP Power Transistors

2SA886

## DESCRIPTION

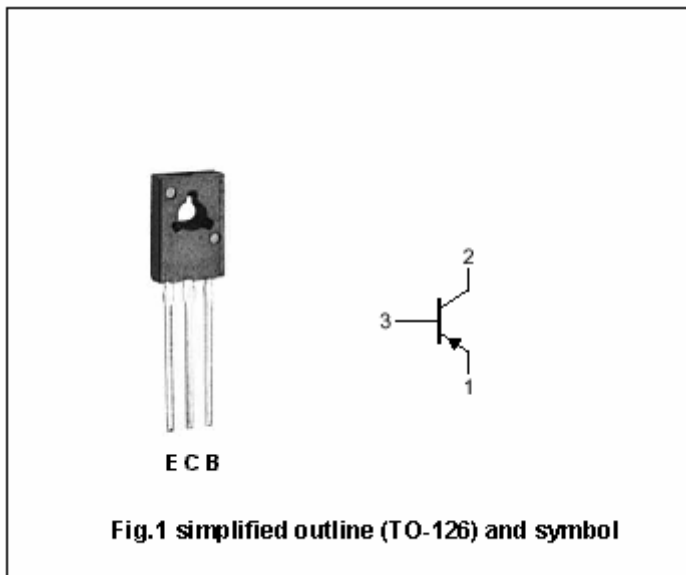
- With TO-126 package
- Complement to type 2SC1847
- Low collector-emitter saturation voltage

## APPLICATIONS

- For low-frequency power amplification

## PINNING

| PIN | DESCRIPTION                          |
|-----|--------------------------------------|
| 1   | Emitter                              |
| 2   | Collector;connected to mounting base |
| 3   | Base                                 |



## Absolute Maximun Ratings (Ta=25℃)

| SYMBOL    | PARAMETER                   | CONDITIONS               | VALUE      | UNIT               |
|-----------|-----------------------------|--------------------------|------------|--------------------|
| $V_{CBO}$ | Collector-base voltage      | Open emitter             | -50        | V                  |
| $V_{CEO}$ | Collector-emitter voltage   | Open base                | -40        | V                  |
| $V_{EBO}$ | Emitter-base voltage        | Open collector           | -5         | V                  |
| $I_C$     | Collector current           |                          | -1.5       | A                  |
| $I_{CM}$  | Collector current-peak      |                          | -3.0       | A                  |
| $P_C$     | Collector power dissipation | $T_C=25^{\circ}\text{C}$ | $1.2^{*1}$ | W                  |
|           |                             |                          | $5^{*2}$   |                    |
| $T_j$     | Junction temperature        |                          | 150        | $^{\circ}\text{C}$ |
| $T_{stg}$ | Storage temperature         |                          | -55~150    | $^{\circ}\text{C}$ |

Note) \*1: Without heat sink

\*2: With a 100 × 100 × 2 mm A1 heat sink

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## CHARACTERISTICS

Tj=25°C unless otherwise specified

| SYMBOL        | PARAMETER                            | CONDITIONS                       | MIN | TYP. | MAX  | UNIT    |
|---------------|--------------------------------------|----------------------------------|-----|------|------|---------|
| $V_{(BR)CEO}$ | Collector-emitter breakdown voltage  | $I_C=-2mA; I_B=0$                | -40 |      |      | V       |
| $V_{(BR)CBO}$ | Collector-base breakdown voltage     | $I_C=-1mA; I_E=0$                | -50 |      |      | V       |
| $V_{CEsat}$   | Collector-emitter saturation voltage | $I_C=-1.5A; I_B=-0.15A$          |     |      | -1.0 | V       |
| $V_{BEsat}$   | Base-emitter saturation voltage      | $I_C=-2A; I_B=-0.2A$             |     |      | -1.5 | V       |
| $I_{CBO}$     | Collector cut-off current            | $V_{CB}=-20V; I_E=0$             |     |      | -1   | $\mu A$ |
| $I_{CEO}$     | Collector cut-off current            | $V_{CE}=-10V; I_B=0$             |     |      | -100 | $\mu A$ |
| $I_{EBO}$     | Emitter cut-off current              | $V_{EB}=-5V; I_C=0$              |     |      | -10  | $\mu A$ |
| $h_{FE}$      | DC current gain                      | $I_C=-1A; V_{CE}=-5V$            | 80  |      | 220  |         |
| $C_{OB}$      | Output capacitance                   | $I_E=0; V_{CB}=-20V; f=1MHz$     |     | 45   |      | pF      |
| $f_T$         | Transition frequency                 | $I_C=0.5A; V_{CB}=-5V; f=200MHz$ |     | 150  |      | MHz     |

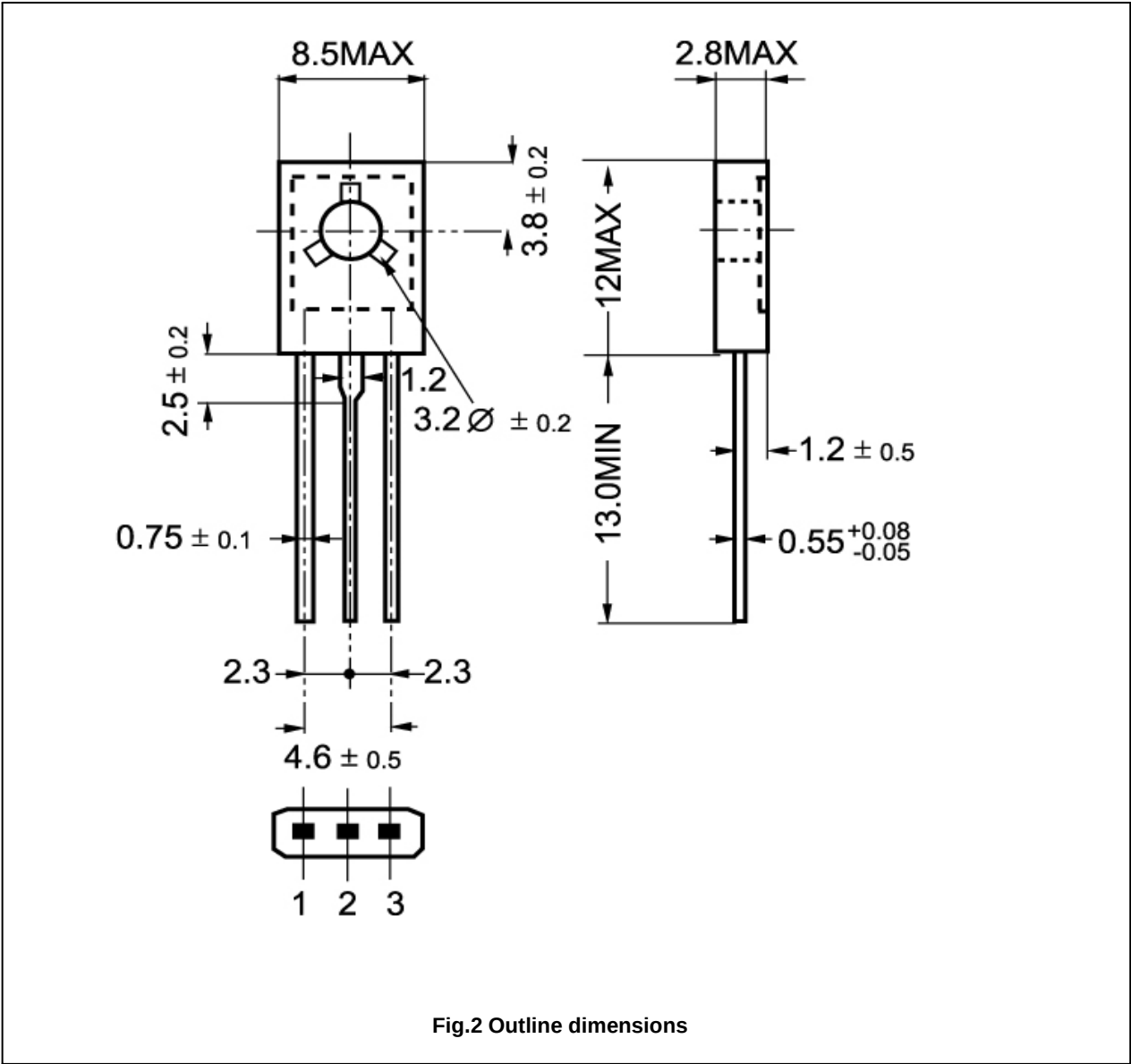
◆  $h_{FE}$  Classifications

| Q      | R       |
|--------|---------|
| 80-160 | 120-220 |

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PACKAGE OUTLINE



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